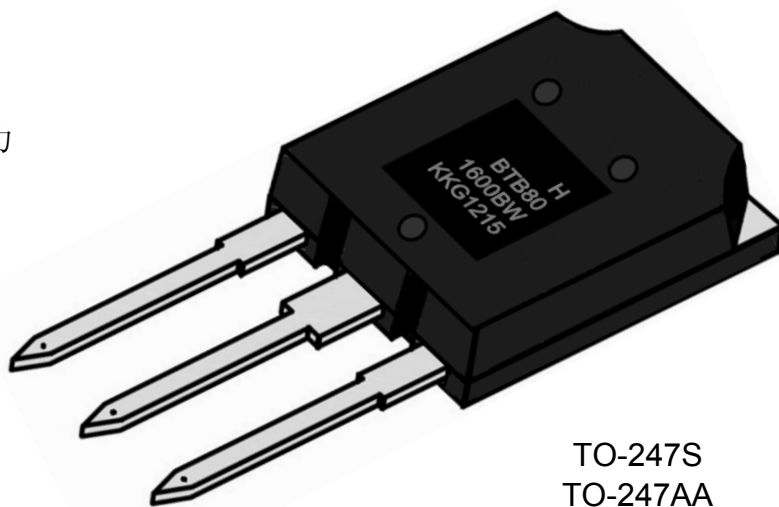


■ 产品特征

- PNPN四层结构硅芯片
- 三象限、三端双向可控硅开关
- 双台面玻璃钝化工艺
- 多层金属化电极提高瞬间浪涌电流承受力
- 较高阻断电压
- 较强抗电流冲击能力

■ 应用领域

- 自动化电气设备
- 交流/直流电源变换
- 电加热控制
- 无功补偿
- 复合开关、大功率路灯
- 大功率捕鱼器
- 电机马达调速控制电路



TO-247S
TO-247AA
Super-247

■ QUICK REFERENCE 【参考特性】

產品型號 Part Number	工業型號 Industry Part №	通態電流均方值 I _{T(RMS)} (A)	斷態重復峰值電壓 V _{DRM} / V _{RRM} (V)	門極觸發電流 I _{GT} (mA)	包裝方式 Packing	元件標識 Marking
BTB80-800BW	BTB80-800BW	80 A	800 V	型号后綴 B: I _{GT} ≤ 50mA W: 3-Q 3 Quadrants Triacs	30Pcs/Tube 450Pcs/Box 每管30只 每盒450只	H BTB80 1600B KKG1215 H: HAOHAI KKG:注册商標 1215:生产日期 2012年第15周出廠 按实际自然周
BTB80-1000BW	BTB80-1000BW		1000 V			
BTB80-1200BW	BTB80-1200BW		1200 V			
BTB80-1400BW	BTB80-1400BW		1400 V			
BTB80-1600BW	BTB80-1600BW		1600 V			
BTB80-1800BW	BTB80-1800BW		1800 V			
① 三象限、大电流、高压、特殊机种 ② 1200V、1600V 常规出货，其它高压需订制 ③ 触发电流I _{GT} 值可按客户要求订制					6.5g / Pcs 每枚重量6.5克	

■ PINNING: TO-247AA (Super-247) 【TO-247直插半塑封】【BTB為非絕緣型: 中間管腳T2與散熱片Tab導通】

Pin 管腳排列	Symbol 對應極性	Description 極性名詞	Description 極性含義	Practicality in Pin Arrange 元件實物與管腳排列	Pin Polarity Circuit diagram 腳位與極性 電路符號表示
1	T1	Main terminal 1	第一陽極		
2	T2	Main terminal 2	第二陽極		
3	G	Gate	門-控制極		
4	Tab	---	散熱片		

■ ABSOLUTE RATINGS (Limiting Values) 【額定值參數】

SYMBOL 符號表示	Parameter & Test Conditions 器件符號含義及參數測試條件說明		Value 數值	Unit 單位	
$I_{T(RMS)}$	通態電流均方值: On-State RMS Current (full sine wave, $T_c=70^\circ\text{C}$)		80	A	
I_{TSM}	通態浪湧電流 Non repetitive surge peak on-state current		$t_p=10\text{ms}, f=50\text{Hz}$		800
			$t_p=8.3\text{ms}, f=60\text{Hz}$		852
I_{GM}	控制極峰值散耗電流: $t_p=20\mu\text{s}, T_c=125^\circ\text{C}$		8	W	
I^2t	週期電流平方時間積: Circuit Fusing Consideration ($t_p=10\text{mS}$)		3200		
P_{GM}	控制極峰值散耗功率: $t_p=20\mu\text{s}, T_c=125^\circ\text{C}$		10	W	
$P_{G(AV)}$	門極平均散耗功率: Average gate power ($T_j=125^\circ\text{C}$)		2.0		
V_{DRM}	斷態重復峰值電壓	參考型號對照列表 Repetitive peak off-state voltages ($T_j=25^\circ\text{C}$)	800~1800	V	
V_{RRM}	反向重復峰值電壓				
T_j	工作結溫: Operating Junction Temperature Range @ Rate V_{RRM} and V_{DRM}		-40 ~ +125	°C	
T_{stg}	貯存溫度: Storage Temperature Range		-40 ~ +150		
T_L	引腳承受焊錫極限溫度: Maximum Lead Temperature for Soldering Purposes 1/8 from Case for 10 Seconds		300		

■ ELECTRICAL CHARACTERISTICS (Tj=25°C Unless Otherwise Noted) 【電參數】

SYMBOL 符號表示	Parameter & Test Conditions 符號含義及參數測試條件說明		Value			Unit 單位
			最小值	典型值	最大值	
$I_{GT I (T2+G+)}$	門極觸發電流第一象限	門極觸發電流 Gate trigger current $V_D=12V_{DC}, R_L=33\Omega, T_j=25^\circ\text{C}$	--	--	50	mA
$I_{GT II (T2+G-)}$	門極觸發電流第二象限		--	--	50	
$I_{GT III (T2-G-)}$	門極觸發電流第三象限		--	--	50	
I_H	維持電流: Holding Current	$I_T=100\text{mA}$	--	--	60	
I_L	擎柱電流 Latching Current ($I_G=1.2 I_{GT}$)	$I_{GT I} I_{GT III}$	--	--	80	
		$I_{GT II}$	--	--	100	
I_{DRM}	斷態重復峰值電流 Latching Current ($V_D=V_{DRM}, V_R=V_{DRM}$)	$T_j=25^\circ\text{C}$	--	--	50	µA
I_{RRM}		$T_j=125^\circ\text{C}$	--	--	1000	
V_{GT}	門極觸發電壓: Gate trigger voltage ($V_D=12V_{DC}, R_L=33\Omega, T_j=25^\circ\text{C}$)		--	--	1.3	V
V_{GD}	門極不觸發電壓: Gate NO-trigger voltage ($V_D=V_{DRM}, R_L=33\Omega, T_j=25^\circ\text{C}$)		0.2	--	--	
V_{TM}	通態峰值電壓: Peak Forward On-State Voltage ($I_{TM}=120\text{A}, t_p=380\mu\text{s}, T_j=25^\circ\text{C}$)		--	--	1.55	
dv/dt	斷態臨界電壓上升率: Critical Rate of Rise of Off-State Voltage		1000	--	--	V/µs
di/dt	通態臨界電流上升率: Critical Rate of Rise of On-State Current		--	--	100	A/µs
$R_{th(j-c)}$	熱阻-結到外殼: Thermal Resistance-Junction-to-Case		--	0.35	--	°C/W
$R_{th(j-a)}$	熱阻-結到環境: Thermal Resistance-Junction-to-Ambient		--	40	--	

Figure 1: Maximum power dissipation versus RMS on-state current (full cycle)

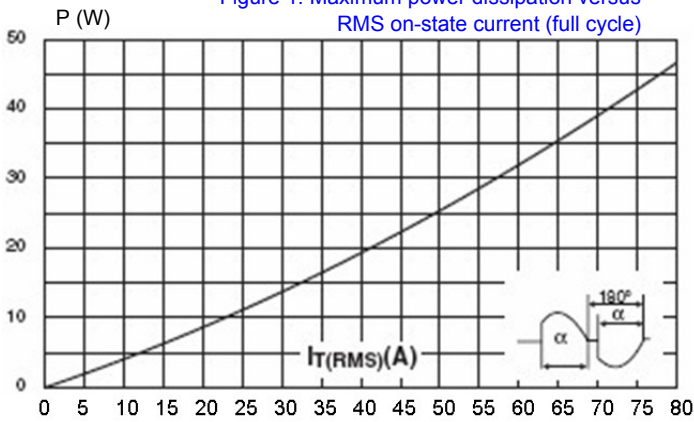


Figure 2: RMS on-state current versus case temperature (full cycle)

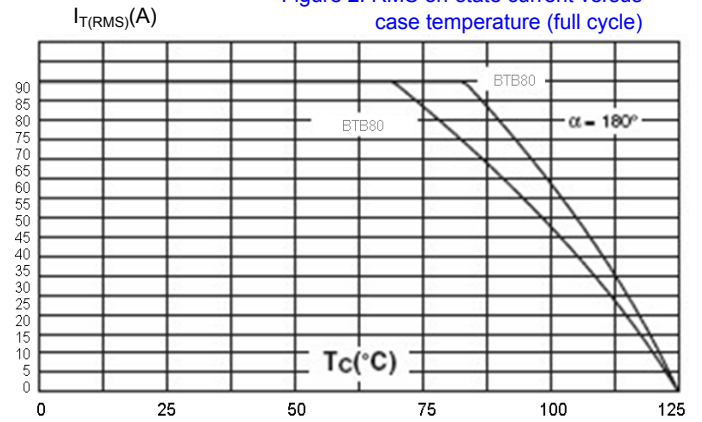


Figure 3: Relative variation of thermal impedance versus pulse duration

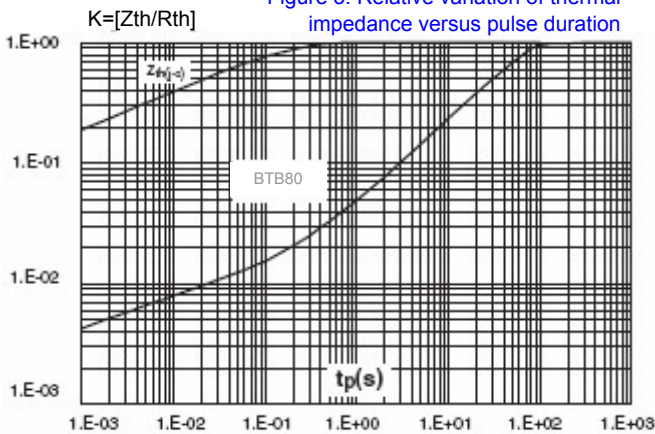


Figure 4: On-state characteristics (maximum) values

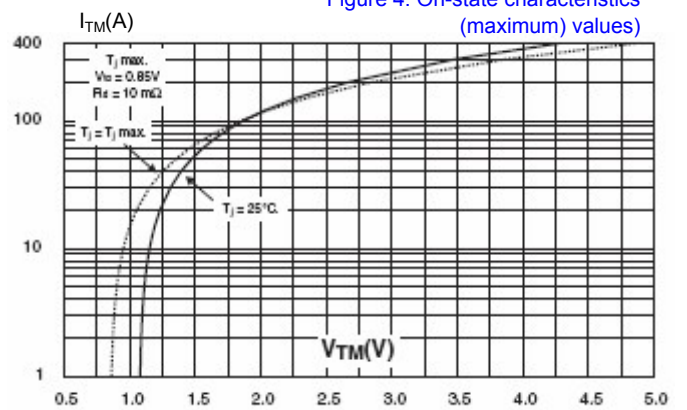


Figure 5: Surge peak on-state current versus number of cycles

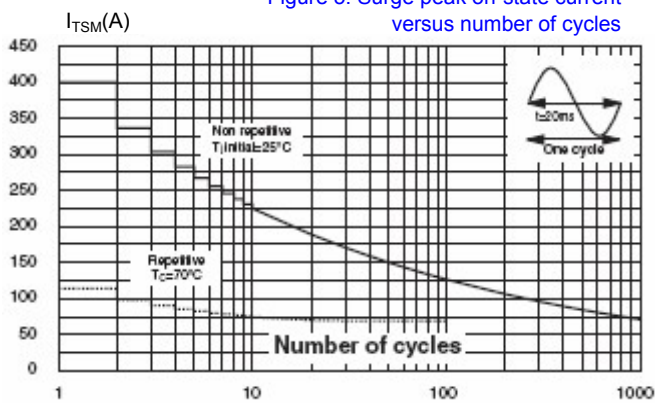


Figure 6: Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp < 10 ms and corresponding value of I²t

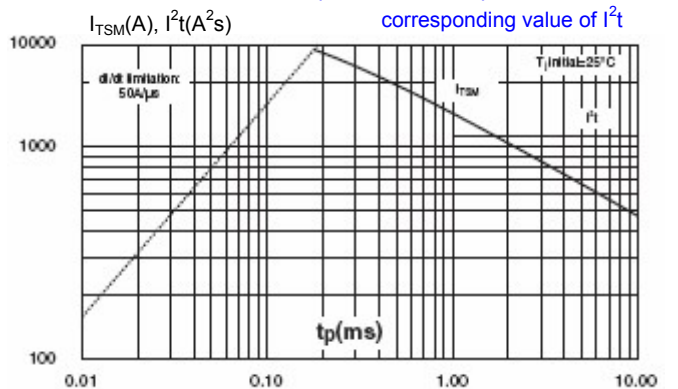


Figure 7: Relative variation of gate trigger current, holding current and latching current versus junction temperature (typical values)

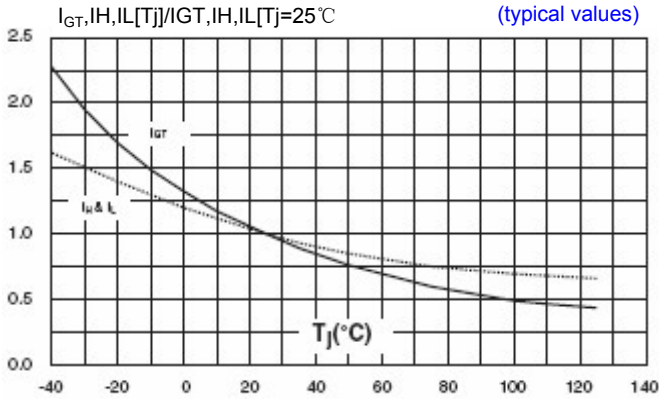


Figure 8: Relative variation of critical rate of decrease of main current versus $(dV/dt)_c$ (typical values)

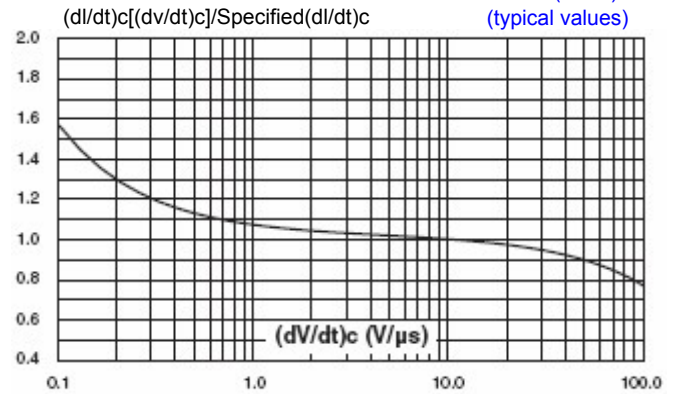
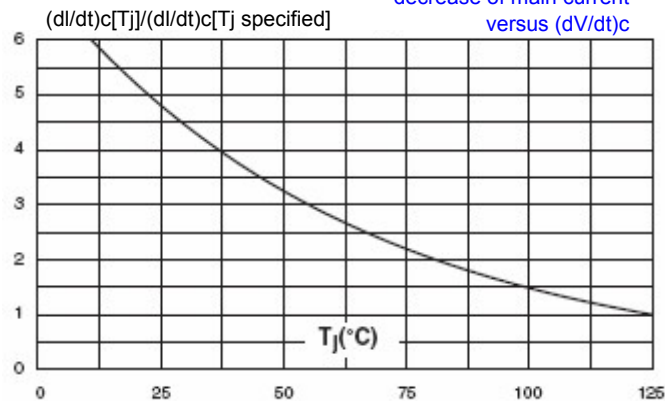
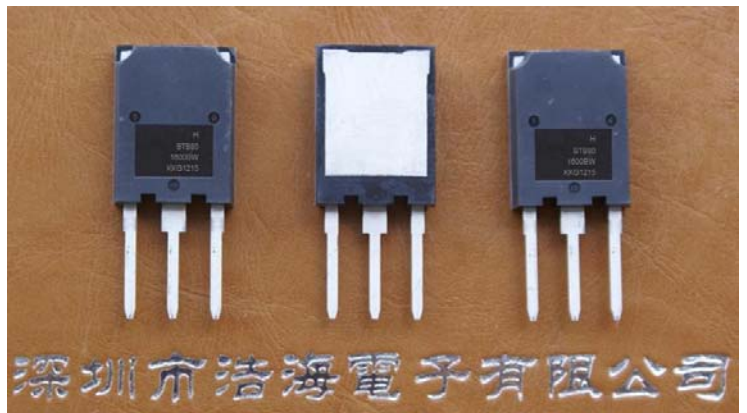


Figure 9: Relative variation of critical rate of decrease of main current versus $(dV/dt)_c$



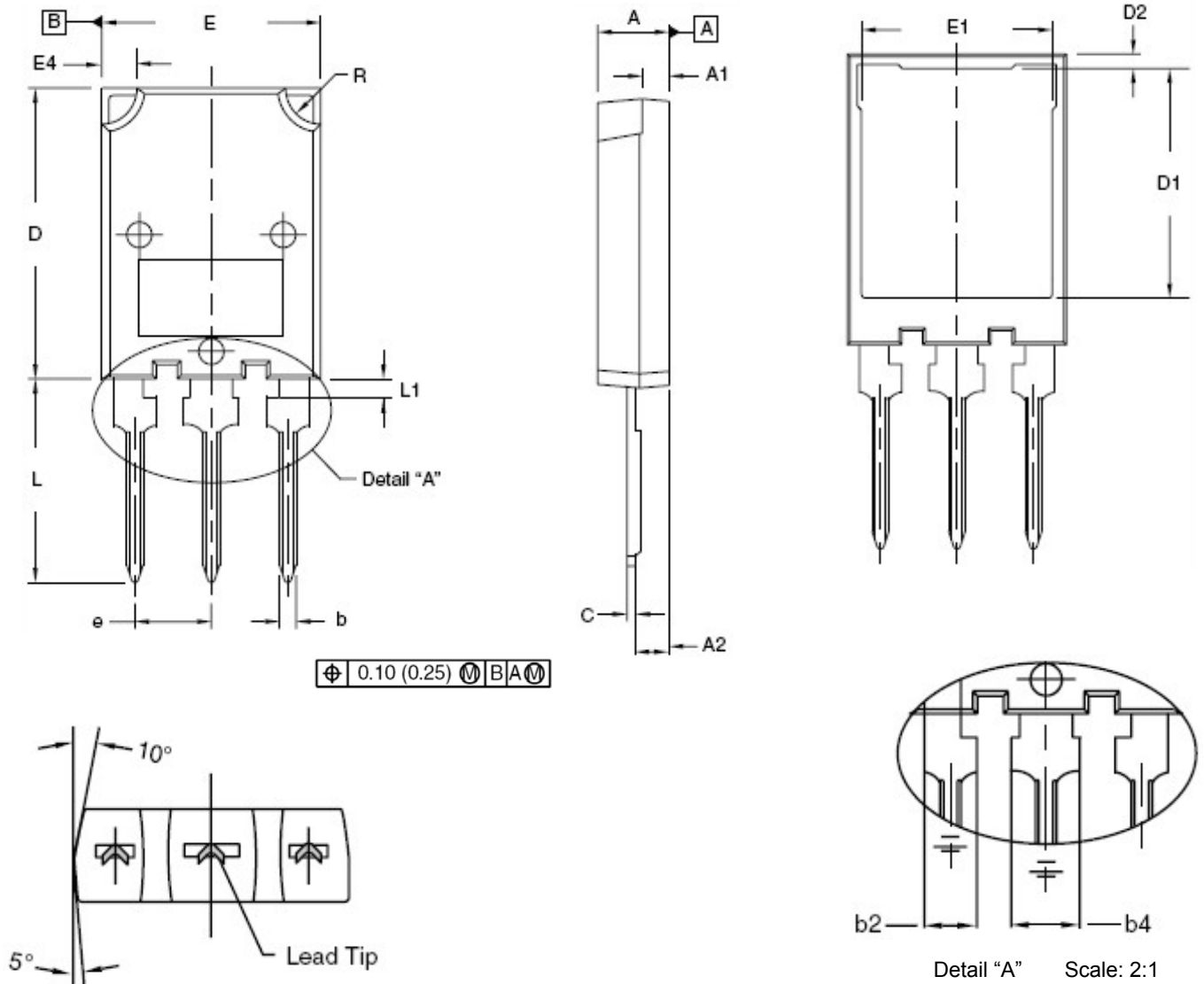
Component physical picture

元件实物图



Package Information (mm & Inches)

TO-247AA (Super-247) 封装尺寸 單位: 毫米與英寸對照 mm & Inches



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.70	5.30	0.185	0.209
A1	1.50	2.50	0.059	0.098
A2	2.25	2.65	0.089	0.104
b	1.30	1.60	0.051	0.063
b2	1.80	2.20	0.071	0.087
b4	3.00	3.25	0.118	0.128
c	0.80	1.20	0.031	0.047
D	19.80	20.80	0.780	0.819

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D1	15.50	16.10	0.610	0.634
D2	0.700	1.300	0.028	0.051
E	15.10	16.10	0.594	0.634
E1	13.30	13.90	0.524	0.547
e	5.45 BSC		0.215 BSC	
L	13.70	14.70	0.539	0.579
L1	1.000	1.600	0.039	0.063
R	2.000	3.000	0.079	0.118



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